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FFSP1065A

Silicon Carbide Schottky Diode 650 V, 10 A

Features

- Max Junction Temperature 175 °C
- · Avalanche Rated 64 mJ
- · High Surge Current Capacity
- · Positive Temperature Coefficient
- · Ease of Paralleling
- · No Reverse Recovery / No Forward Recovery

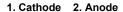
Applications

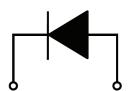
- · General Purpose
- · SMPS, Solar Inverter, UPS
- · Power Switching Circuits

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.







1. Cathode 2. Anode

Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter	FFSP1065A	Unit		
V_{RRM}	Peak Repetitive Reverse Voltage		650	V	
E _{AS}	Single Pulse Avalanche Energy	(Note 1)	64	mJ	
I _F	Continuous Rectified Forward Current @ T _C < 152 °C		10	A	
	Continuous Rectified Forward Current @ Tc < 135 °C		15		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25 °C, 10 μs	760	Α	
		T _C = 150 °C, 10 μs	740	Α	
I _{F,SM}	Non-RepetitiveForwardSurgeCurrent	Half-Sine Pulse, t _p = 8.3 ms	56	Α	
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	38	Α	
Ptot	Dougs Dissination	T _C = 25 °C	111	W	
	Power Dissipation	T _C = 150 °C	19	W	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.35	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSP1065A	FFSP1065A	TO-220-2L	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _F	Forward Voltage	I _F = 10 A, T _C = 25 °C	-	1.50	1.75	V
		$I_F = 10 \text{ A}, T_C = 125 {}^{\circ}\text{C}$	-	1.6	2.0	
		$I_F = 10 \text{ A}, T_C = 175 ^{\circ}\text{C}$	-	1.72	2.4	
I _R	Reverse Current	$V_R = 650 \text{ V}, T_C = 25 ^{\circ}\text{C}$	-	-	200	μА
		$V_R = 650 \text{ V}, T_C = 125 ^{\circ}\text{C}$	-	-	400	
		$V_R = 650 \text{ V}, T_C = 175 ^{\circ}\text{C}$	-	-	600	
Q_C	Total Capacitive Charge	V = 400 V	-	34	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	575	-	pF
		$V_R = 200 \text{ V, f} = 100 \text{ kHz}$	-	62	-	
		$V_R = 400 \text{ V}, f = 100 \text{ kHz}$	-	47	-	

Typical Characteristics $T_J = 25$ °C unless otherwise noted.

Figure 1. Forward Characteristics 10 I, FORWARD CURRENT (A) T_J = 175 °C T_J = 125 °C 0.0 0.0 0.5 2.0 1.0 V_{F} , FORWARD VOLTAGE (V)

Figure 3. Current Derating

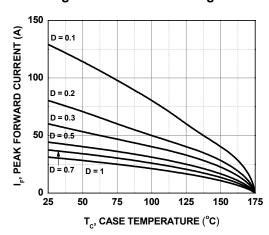


Figure 2. Reverse Characteristics

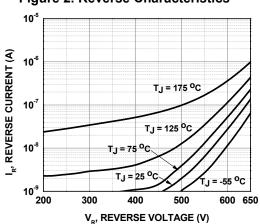
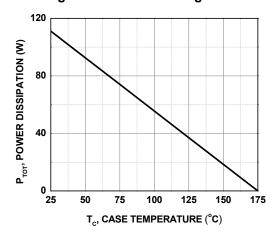


Figure 4. Power Derating



Notes: 1: E_{AS} of 64 mJ is based on starting T_J = 25 °C, L = 0.5 mH, I_{AS} = 16 A, V = 50 V.

Typical Characteristics $T_J = 25$ °C unless otherwise noted.

Figure 5. Capacitive Charge vs. Reverse Voltage

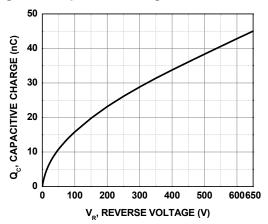


Figure 6. Capacitance vs. Reverse Voltage

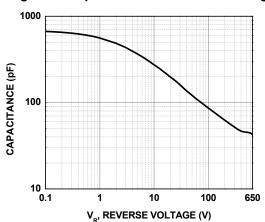


Figure 7. Capacitance Stored Energy

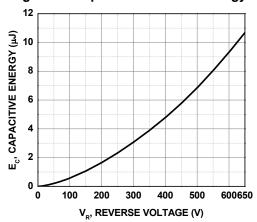
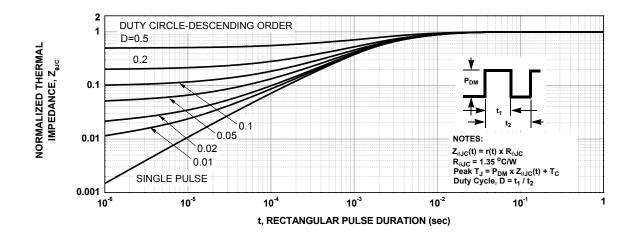
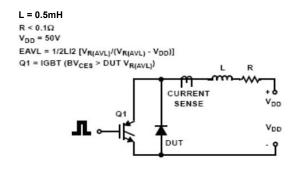


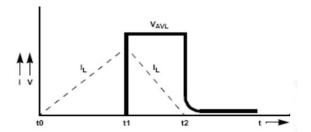
Figure 8. Junction-to-Case Transient Thermal Response Curve



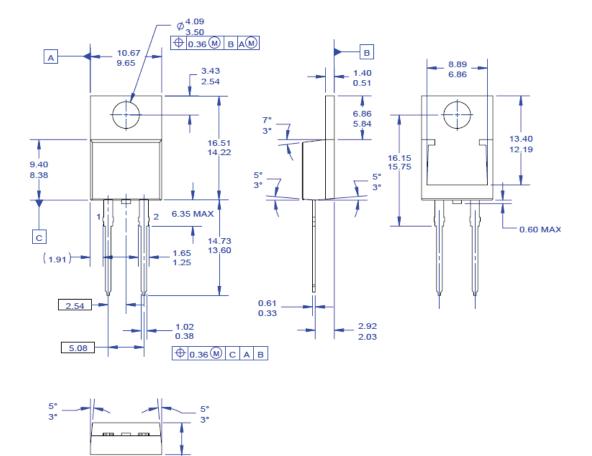
Test Circuit and Waveforms

Figure 9. Unclamped Inductive Switching Test Circuit & Waveform





Mechanical Dimensions



NOTES:

A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002. B. ALL DIMENSIONS ARE IN MILLIMETERS.

4.80 4.30

- DIMENSION AND TOLERANCE AS PER ASME
- Y14.5-2009
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS. E. DRAWING FILE NAME: TO220A02REV5

Figure 10. TO-220 2L - TO-220, MOLDED, 2LD

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